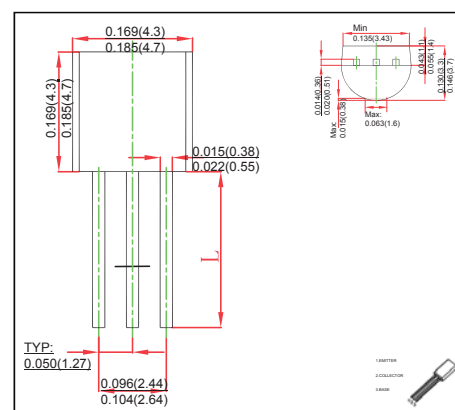


**TO-92 Plastic-Encapsulate Transistors**
**FEATURES**

- Power switching applications
- TRANSISTOR( NPN )

**MECHANICAL DATA**

- Case style:TO-92 molded plastic
- Mounting position:any


**MAXIMUM RATINGS AND CHARACTERISTICS**

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	700	V
Collector-Emitter Voltage	VCEO	400	V
Emitter-Base Voltage	VEBO	9	V
Collector Current -Continuous	IC	1.5	A
Collector Power Dissipation	PC	0.9	W
Junction Temperature	TJ	150	°C
Storage Temperature	Tstg	-55 ~+150	°C

**Electrical Specification(T<sub>A</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 1mA, IE=0	700			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 10mA, IB=0	400			V
Emitter-base breakdown voltage	V(BR)EBO	IE= 1mA, IC=0	9			V
Collector cut-off current	ICBO	VCB= 700V, IE=0			100	μA
Collector cut-off current	ICEO	VCE= 400V, IB=0			50	μA
Emitter cut-off current	IEBO	VEB= 7V, IC=0			10	μA
DC current gain	hFE	VCE= 10V, IC= 0.4 A	20		40	
Collector-emitter saturation voltage	VCE(sat)1	IC=1.5A,IB= 0.5A			3	V
	VCE(sat)2	IC=1.5A,IB= 0.5A			0.8	V
Base-emitter saturation voltage	VBE(sat)	IC=0.5A, IB=0.1A			1	V
Transition Frequency	fT	VCE= 10V, IC= 100mA,f=1MHz	4			MHz
Fall time	tf	IC=1A			0.7	μs
Storage time	ts	IB1=-IB2=0.2A			4	μs

# RATINGS AND CHARACTERISTIC CURVES

Static Characteristic

